

**WHAT IS CLAIMED IS:**

1. A method comprising:  
forming a tungsten plug in a dielectric layer;  
forming an electrically conductive interconnect line on the dielectric layer after the formation of the tungsten plug in the dielectric layer, wherein the tungsten plug is electrically connected to the electrically conductive interconnect line;  
exposing the electrically conductive interconnect line with ionized air after the formation of the electrically conductive interconnect line.
2. The method of claim 1 further comprising contacting the electrically conductive interconnect line with a solution to remove residual polymer after the electrically conductive interconnect line is exposed to ionized air.
3. The method of claim 2, wherein the liquid is one that is able to remove a photoresist material from the electrically conductive line.
4. The method of claim 1, further comprising exposing the electrically conductive interconnect line with ionized air during a transfer of a wafer in a wafer transfer system, wherein the electrically conductive interconnect line is included on the wafer.
5. The method of claim 1, wherein exposing the electrically conductive interconnect line to ionized air comprises exposing the electrically conductive interconnect line with at least one of positive ions and negative ions.
6. The method of claim 5, wherein exposing the electrically conductive interconnect line with ionized air comprises exposing the electrically conductive interconnect line with at least one of oxygen ions, nitrogen ions, carbon dioxide ions, and argon ions.
7. The method of claim 1, wherein exposing the electrically conductive interconnect line with ionized air comprises creating positive and/or negative ions in air around the electrically conductive interconnect line.

8. The method of claim 7, wherein exposing the electrically conductive interconnect line with ionized air comprises creating positive and/or negative ions in air from a point approximately 1 meter from the electrically conductive interconnect line.

9. The method of claim 1, further comprising exposing the electrically conductive interconnect line with ionized air after the formation of the electrically conductive interconnect line for approximately 60 seconds or less.

10. The method of claim 1 wherein the electrically conductive interconnect line is included on the wafer, and wherein the wafer is moving relative to a source of the ionized air as the electrically conductive interconnect line is exposed with ionized air.

11. The method of claim 1 wherein the electrically conductive interconnect line is included on the wafer, and wherein the wafer is stationary relative to a source of the ionized air as the electrically conductive interconnect line is exposed with ionized air.

12. The method of claim 1 wherein the electrically conductive interconnect line is included on a wafer surface, and wherein the wafer surface faces a source of the ionized air.

13. The method of claim 1 wherein the electrically conductive interconnect line is included on a wafer surface, and wherein the wafer surface is parallel to a stream of the ionized air.

14. An integrated circuit produced by a method comprising:  
forming a tungsten plug in a dielectric layer;  
forming an electrically conductive interconnect line on the dielectric layer after the formation of the tungsten plug in the dielectric layer, wherein the tungsten plug is electrically connected to the electrically conductive interconnect line;  
exposing the electrically conductive interconnect line with ionized air after the formation of the electrically conductive interconnect line.

15. The integrated circuit of claim 14, wherein the method further comprises contacting the electrically conductive interconnect line with a solution to remove residual polymer after exposing the electrically conductive interconnect line with ionized air.

16. The integrated circuit of claim 15, wherein the liquid is one that is able to remove a photoresist material from the electrically conductive line.

17. The integrated circuit of claim 14, wherein the method further comprises exposing the electrically conductive interconnect line with ionized air during a transfer of a wafer in a wafer transfer system, wherein the electrically conductive interconnect line is included on the wafer.

18. The integrated circuit of claim 14, wherein the method further comprises exposing the electrically conductive interconnect line with at least one of positive ions and negative ions.

19. The integrated circuit of claim 18, wherein the method further comprises exposing the electrically conductive interconnect line with at least one of oxygen ions, nitrogen ions, carbon dioxide ions, and argon ions.

20. The integrated circuit of claim 14, wherein exposing the electrically conductive interconnect line with ionized air comprises creating positive and/or negative ions in air around the electrically conductive interconnect line.

21. The integrated circuit of claim 20, wherein the method further comprises exposing the electrically conductive interconnect line with ionized air comprises creating positive and/or negative ions in air from a point approximately 1 meter from the electrically conductive interconnect line.

22. The integrated circuit of claim 14, wherein the method further comprises exposing the electrically conductive interconnect line with ionized air after the formation of the electrically conductive interconnect line for approximately 60 seconds or less.

23. The integrated circuit of claim 14 wherein the electrically conductive interconnect line is included on the wafer, and wherein the wafer is moving relative to a source of the ionized air as the electrically conductive interconnect line is exposed with ionized air.

24. The integrated circuit of claim 14 wherein the electrically conductive interconnect line is included on the wafer, and wherein the wafer is stationary relative to a source of the ionized air as the electrically conductive interconnect line is exposed with ionized air.

25. The integrated circuit of claim 14 wherein the electrically conductive interconnect line is included on a wafer surface, and wherein the wafer surface faces a source of the ionized air.

26. The integrated circuit of claim 14 wherein the electrically conductive interconnect line is included on a wafer surface, and wherein the wafer surface is parallel to a stream of the ionized air.

27. An apparatus comprising:  
a substrate comprising:  
a tungsten plug formed in a dielectric layer;  
an electrically conductive interconnect line formed on the dielectric layer, wherein the tungsten plug is electrically connected to the electrically conductive interconnect line;  
an ionizer for generating ionized air, wherein the ionizer is positioned relative to the substrate so that the electrically conductive interconnect line receives the ionized air.